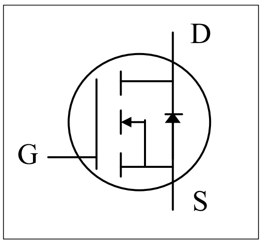
AP10NA8R4P

Halogen-Free Product

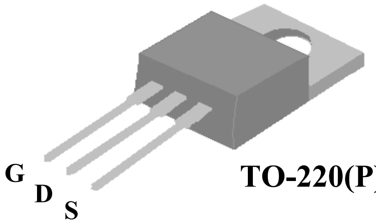
Advanced Power Electronics Corp.

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

- **100% R_g & UIS Test**
- **Simple Drive Requirement**
- **Fast Switching Characteristic**
- **RoHS Compliant & Halogen-Free**



BV_{DSS}	100V
$R_{DS(ON)}$	8.4mΩ
I_D	66A



TO-220(P)

Description

AP10NA8R4 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-220 package is widely preferred for all commercial-industrial through hole applications. The low thermal resistance and low package cost contribute to the worldwide popular package.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V	66	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V	42	A
I_{DM}	Pulsed Drain Current[1]	240	A
P_D@T_C=25℃	Total Power Dissipation	69	W
P_D@T_A=25℃	Total Power Dissipation	2	W
E_{AS}	Single Pulse Avalanche Energy[3]	125	mJ
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.8	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=30A	-	-	8.4	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=30A	-	50	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=$\pm$20V, V_{DS}=0V	-	-	$\pm$0.1	uA
Q_g	Total Gate Charge[4]	I_D=30A	-	42	67.2	nC
Q_{gs}	Gate-Source Charge[4]	V_{DS}=50V	-	12	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge[4]	V_{GS}=10V	-	16	-	nC
$t_{d(on)}$	Turn-on Delay Time[4]	V_{DS}=50V	-	14	-	ns
t_r	Rise Time[4]	I_D=30A	-	70	-	ns
$t_{d(off)}$	Turn-off Delay Time[4]	R_G=7.5Ω	-	30	-	ns
t_f	Fall Time[4]	V_{GS}=10V	-	70	-	ns
C_{iss}	Input Capacitance[4]	V_{GS}=0V	-	2030	3248	pF
C_{oss}	Output Capacitance[4]	V_{DS}=80V	-	300	-	pF
C_{rss}	Reverse Transfer Capacitance[4]	f=1.0MHz	-	20	-	pF
R_g	Gate Resistance	f=1.0MHz	-	0.7	1.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=30A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time[4]	I_S=30A, V_{GS}=0V	-	55	-	ns
Q_{rr}	Reverse Recovery Charge[4]	dI/dt=100A/µs	-	80	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Starting T_j=25°C , V_{DD}=50V , L=0.1mH , R_G=25Ω , V_{GS}=10V

4.Guaranteed by design.

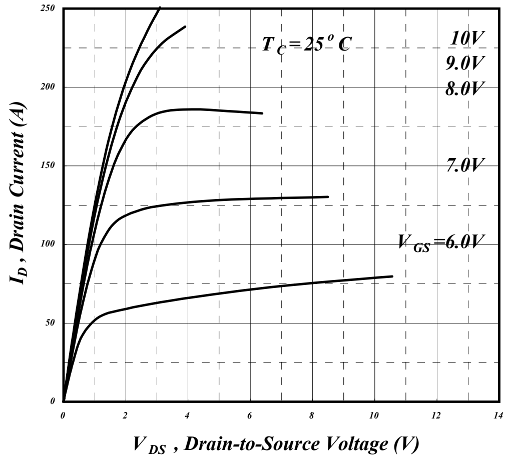


Fig 1. Typical Output Characteristics

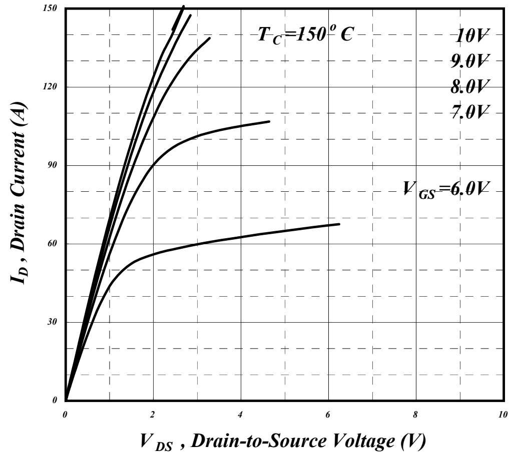


Fig 2. Typical Output Characteristics

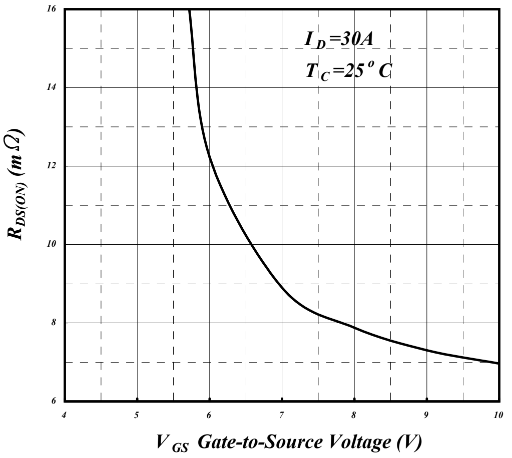


Fig 3. On-Resistance v.s. Gate Voltage

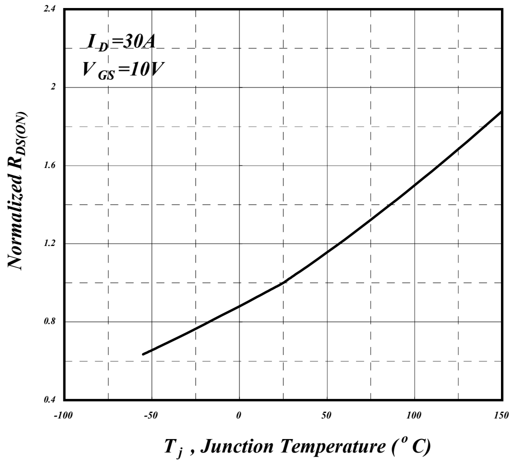


Fig 4. Normalized On-Resistance v.s. Junction Temperature

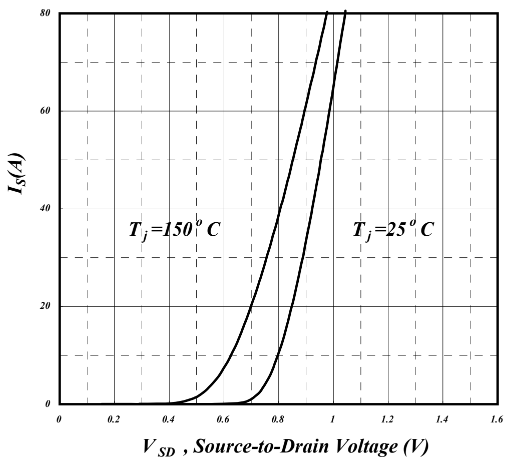


Fig 5. Forward Characteristic of Reverse Diode

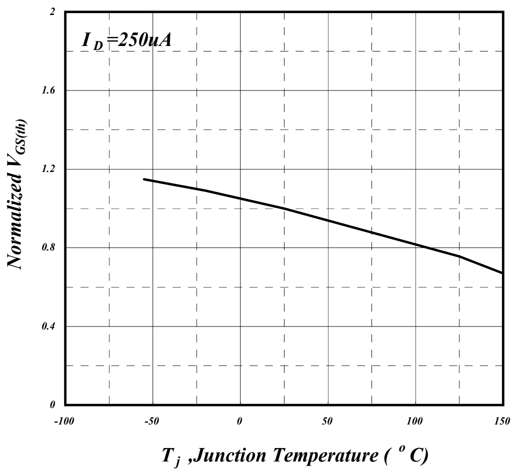


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

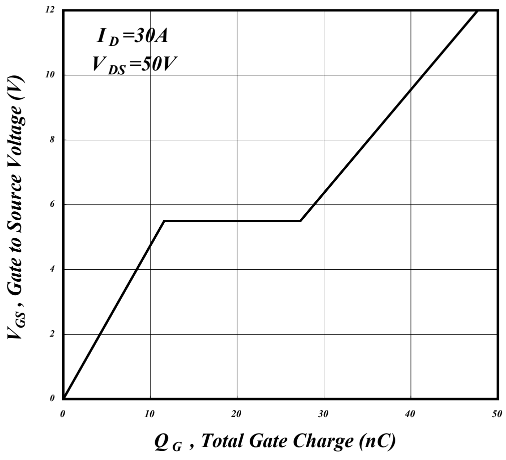


Fig 7. Gate Charge Characteristics

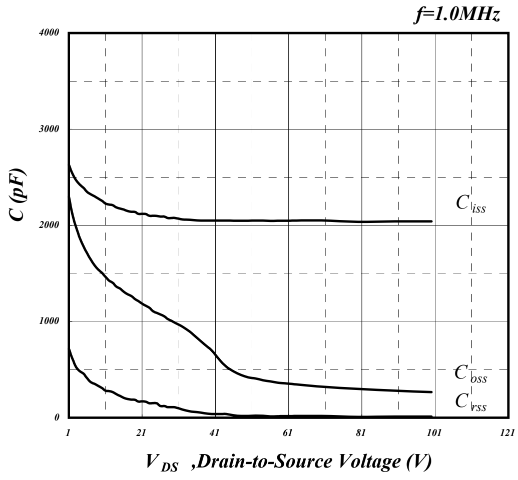


Fig 8. Typical Capacitance Characteristics

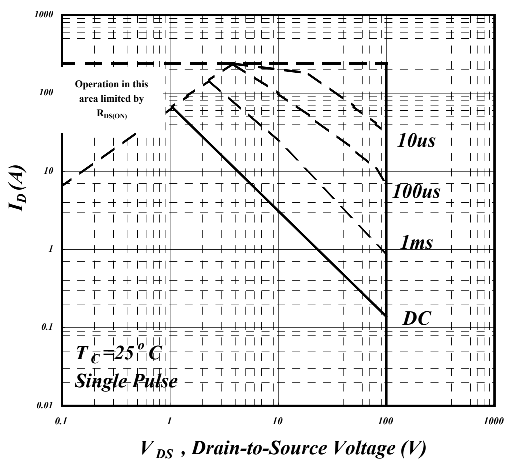


Fig 9. Maximum Safe Operating Area

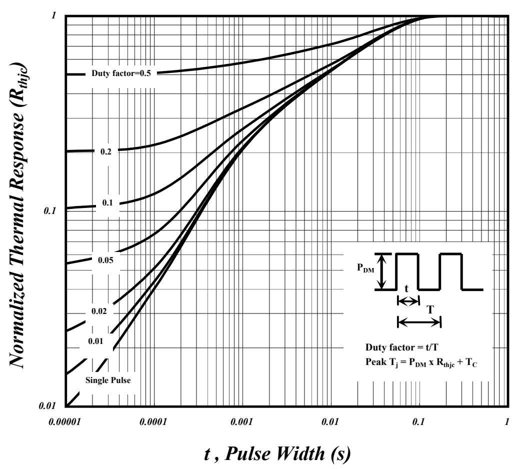


Fig 10. Effective Transient Thermal Impedance

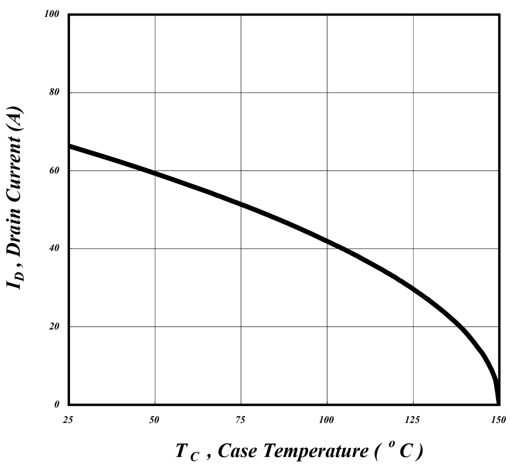


Fig 11. Drain Current v.s. Case Temperature

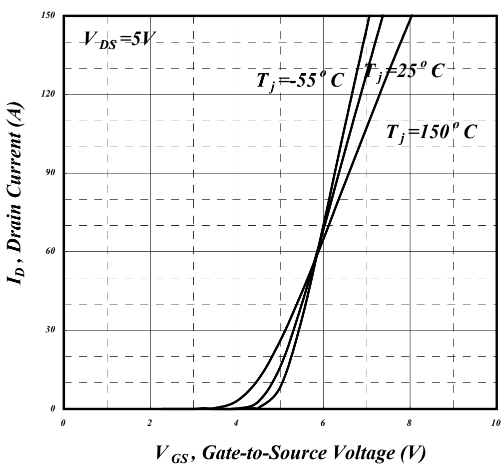


Fig 12. Transfer Characteristics

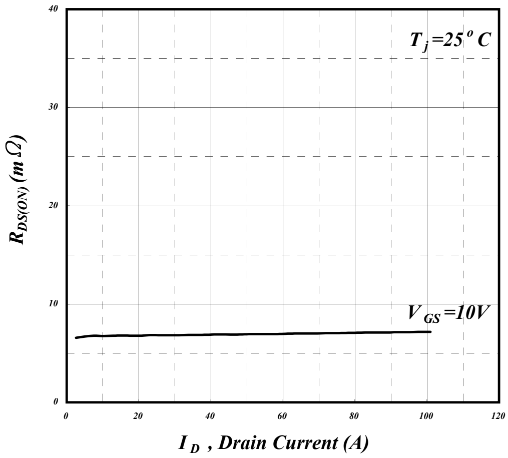


Fig 13. Typ. Drain-Source on State Resistance

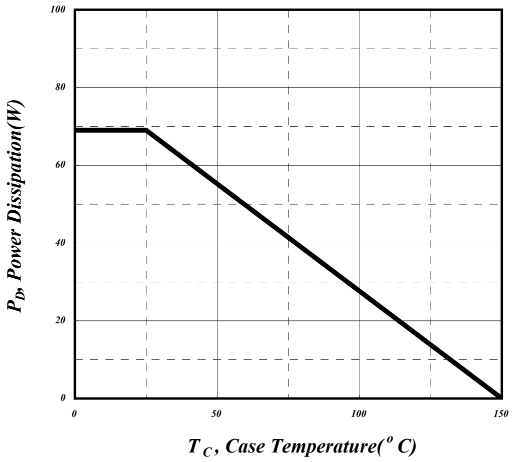


Fig 14. Total Power Dissipation

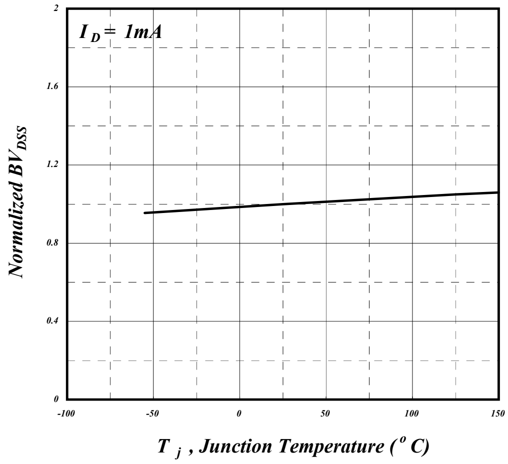


Fig 15. Normalized BV_{DSS} v.s. Junction Temperature

MARKING INFORMATION